	Туре	Hits	Search Text	DBs	Time Stamp
1	BRS	2	6358800.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:06
2	BRS	12	("5434093" "5448094" "5668021" "5780340" "6033980" "6087208" "6100146" "6117712" "6130454" "6171916" "6204128" "6204133").PN.	USPAT	2004/09/12 19:06
3	BRS	1	6358800.URPN.	USPAT	2004/09/12 19:08
4	BRS	9936	transistor with (recess trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
5	BRS		transistor with (recess trench) and etching with isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:42
6	BRS	294	transistor near3 (recess trench) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
7	BRS		(gate transistor) near3 (recess trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
8	BRS	622	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:49
9	BRS	42	<pre>((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:49
10	BRS	758	257/328.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20

•	Туре	Hits	Search Text	DBs	Time Stamp
11 E	3RS	611	257/329.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15
12 E	BRS	984	257/330.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
13 F	BRS	342	257/332.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
14 E	3RS	188	257/334.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15
15 E	BRS	781	257/336.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15
16 E	3RS	239	257/337.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20